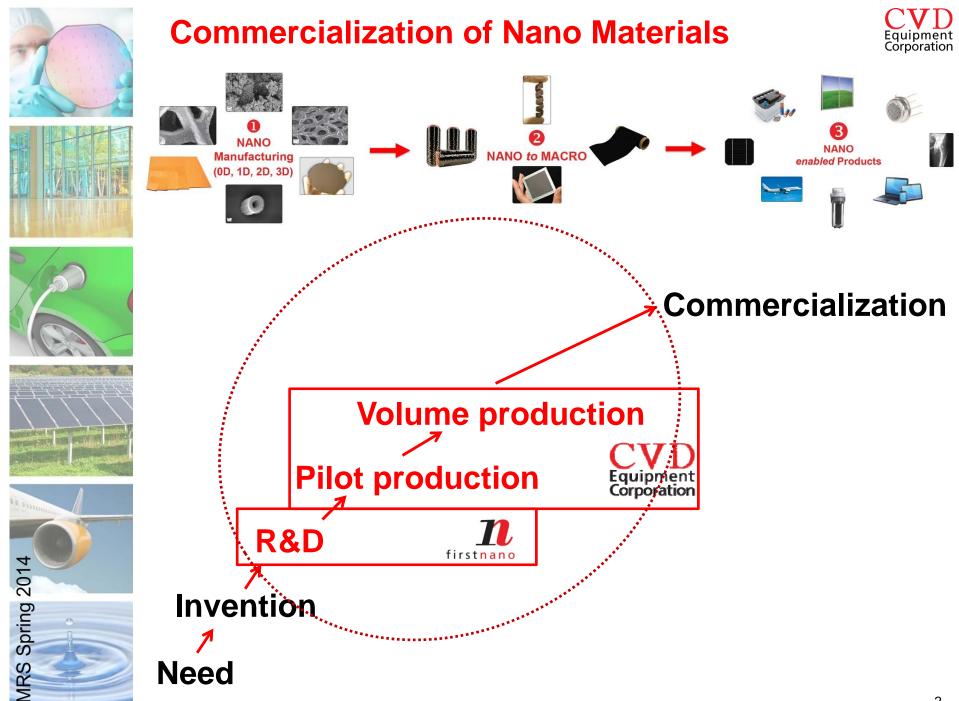


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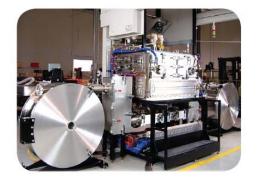




CVD Equipment Corporation

Designs and manufactures both Standard and Configurable R&D, Pilot & Production chemical vapor deposition systems





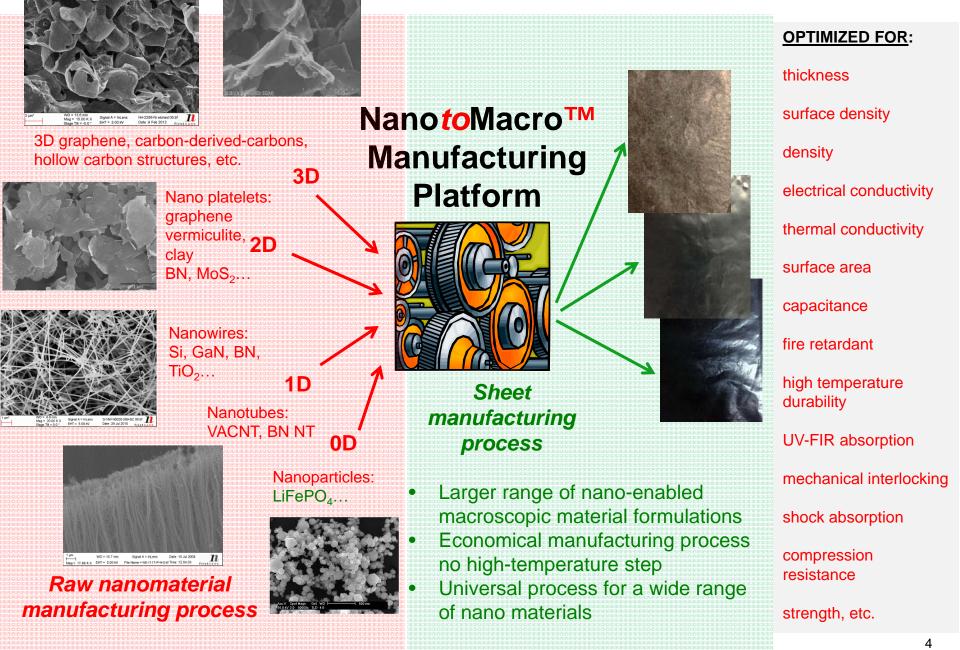


Operate an Application Laboratory:

- Perform contract process development
- Develop process and equipment for research materials
- Work with researchers to help accelerate the commercialization of nanomaterials

Novel Nanoto Macro[™] Manufacturing Platform







NEW EasyGraphene[™] CVD graphene growth platform



















- Scales CVD graphene processes in size and production volume with low execution risk
- Operates with a wider process window to manufacture CVD graphene at lower cost and/or time
- Enables the development of new process windows



Substrate Preparation of Cu foil is very critical For quality improvement of CVD graphene films

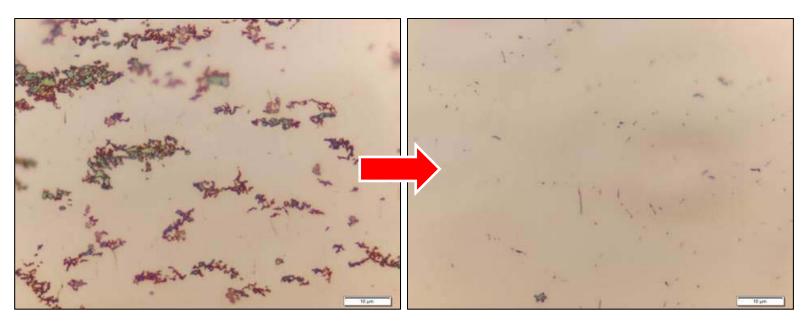












Regular Cu foils, as received from vendor after CVD graphene processing Viewed at 100 X Electropolished Cu foils after CVD graphene processing Viewed at 100 X

Both regular and electropolished Cu foils processed in same CVD graphene process run and removed from oven at 200 °C to increase contrast.

Further optimization of electropolishing or equivalent chemical etching is needed to further improve surface cleanliness and reduce the number of graphene seeds.



EasyGraphene™: Scaling to 300 mm size













Traditional horizontal tube furnace systems can get the Cu foil stuck after 2 hr annealing and 2 hr CVD graphene growth @ 1020 °C and 15 Torr on 18 μ m electropolished Cu foil.





EasyGraphene[™] with proprietary processing technology enables WRINKLE FREE Cu foil processing even for > 5 hr processing time on 300 mm foils.



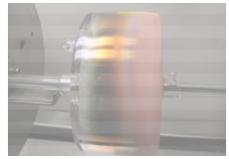
RS Spring 2014

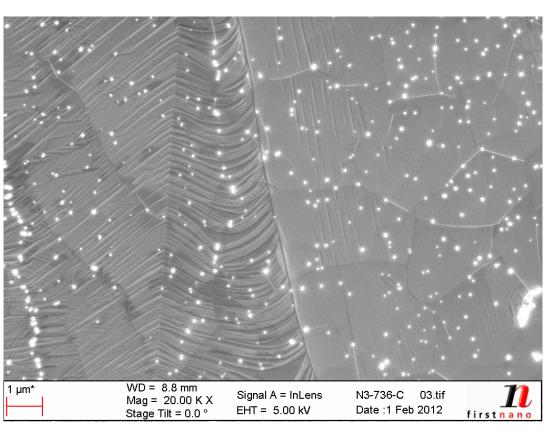
Traditional Systems: Pollution requires frequent maintenance



Traditional horizontal tube furnace systems pollute Cu foil after graphene run: "White dots".

(see OO 4.06, Isaac Ruiz University of California Riverside)





These SiO_2 , CuO_x and other particles problem requires to clean and/or exchange quartz parts often <u>to</u> <u>get repeatable results.</u>



EasyGraphene[™] Processing Technology enables significantly less pollution and maintenance



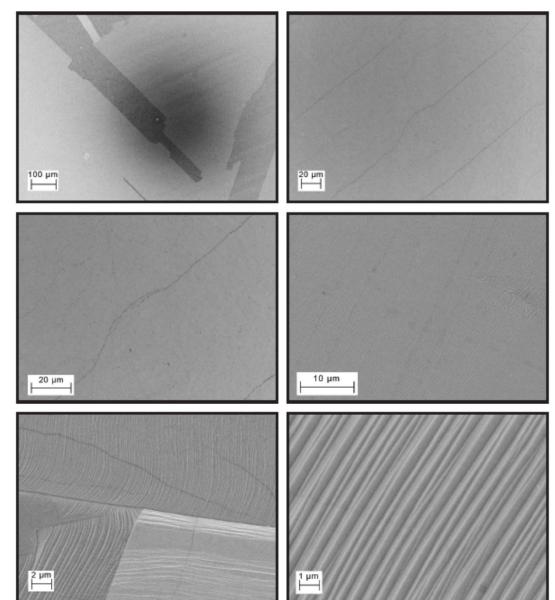


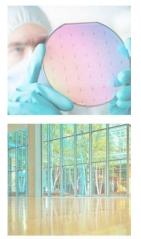


MRS Spring 2014

Reduced Cu deposits on colder parts of the reactor:

- > 1000 X less "white dots"
- 10-100 X less maintenance needed
- SUPER CLEAN CVD graphene surfaces possible with optional hardware and process upgrades





EasyGraphene[™] Processing Technology enables <u>larger Cu grains + smoother Cu foil</u>



300 mm

In general Cu grains of any Cu foil can be increased 100 – 10,000 X.

Up to 300 mm Cu grains have been demonstrated depending on process conditions and Cu foil type.

Cu grain size is limited by Cu foil type and annealing conditions.

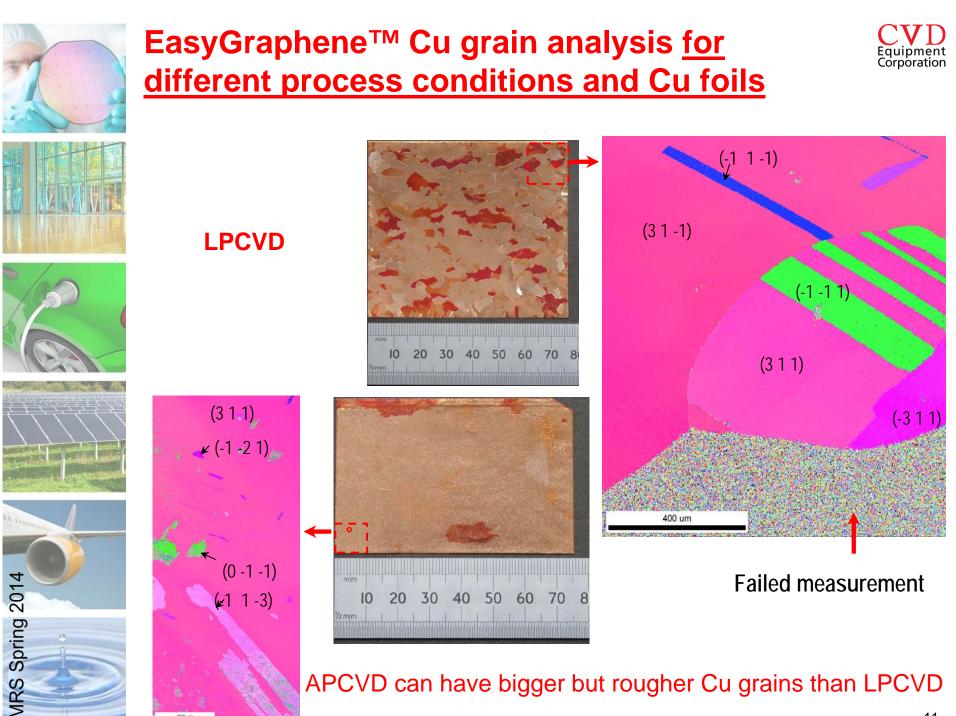
Large Cu grains can be obtained in less time than with traditional CVD graphene systems.



Large Cu grains enable higher quality CVD graphene due to fewer grain boundaries and larger spatial growth regions of Cu. This can lead to higher conductivity/mobility films. Annealed Cu foils removed at 200 °C to oxidized different Cu grains a different rates (colors)









EasyGraphene[™] Processing Technology enables <u>uniform CVD Growth over a large area</u>



Sub-monolayer of CVD graphene film growth, i.e. growth process was terminated before full monolayer coverage.

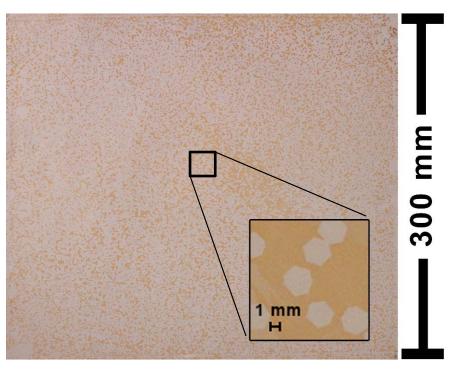


Allows simple process uniformity testing

Image on the right shows 2-3 mm hexagonal CVD graphene grains spread uniformly over 300 mm size Cu foil.



CVD graphene growth uniformity is visible by naked eye - without any instrument. Sample was automatically offloaded at 200 °C to oxidize the non graphene covered Cu foil increasing the optical contrast between graphene islands and substrate.





CVD Equipment Corporation

Some benefits of patent pending technology that have been demonstrated thus far:

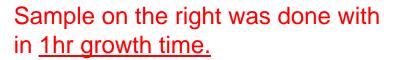
EasyGraphene[™] Processing Technology enables

a wider CVD graphene growth processing window

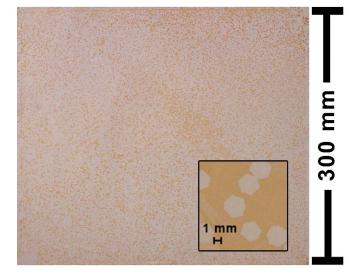
- Operates at low, medium and atmospheric pressure
- Operates at low to high process temperatures
- Substantially independent of total gas flow rate
- Processing cost and time is reduced compared to traditional CVD graphene processes while providing similar results



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This compares to an equivalent <u>5-7 hrs</u> growth time with traditional CVD graphene processes.





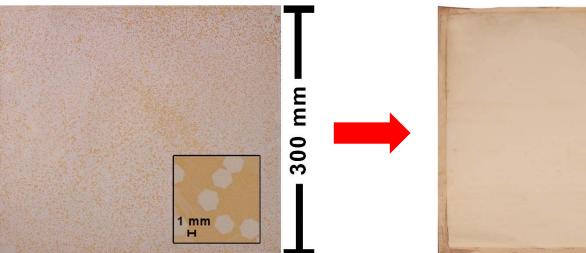
EasyGraphene[™] Processing Technology enables <u>complete CVD graphene growth</u>



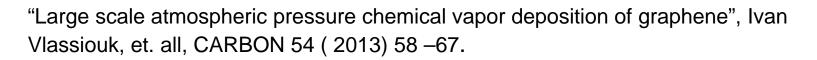




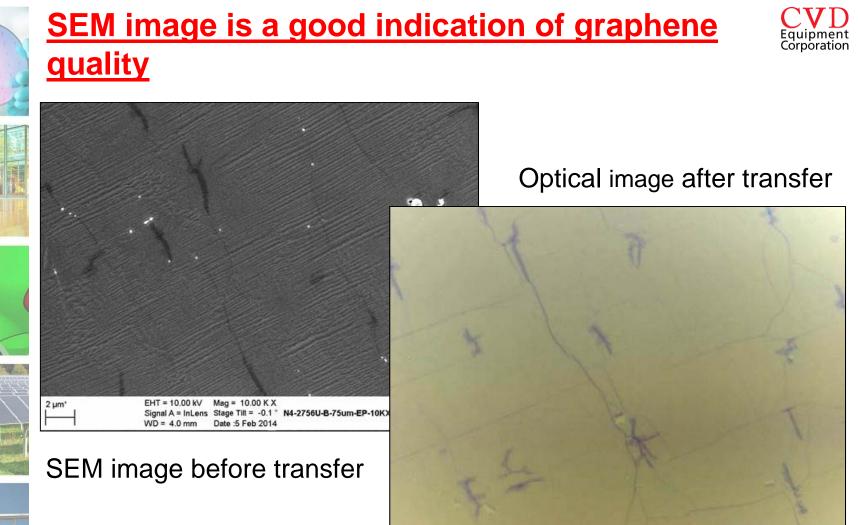
















This rejected CVD graphene sample shows similar multilayer regions before and after graphene transfer using a bubbling electrochemical method.



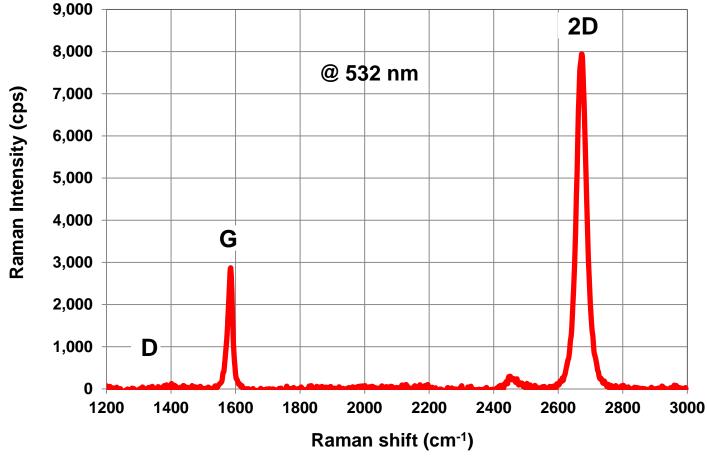
EasyGraphene[™] <u>Raman characterization</u>











Raman spectrum of CVD graphene transferred onto 280 nm SiO₂/Si wafer

After transfer CVD graphene film onto glass shows improved 2D/G peak ratio (>2) due to less interference from the flatter Cu foil surface.

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Summary:

• CVD Equipment Corporation continues to expand capabilities in:

 CVD Application Laboratory supports custom process and material development opportunities to advance the state of the art and pilot

Our EasyGraphene[™] platform is designed for both R&D and pilot production scale-up development efforts. Together with our patent

pending hardware and process solutions it also enables straightforward

- Equipment design
- Process development

production scale-up demonstrations.

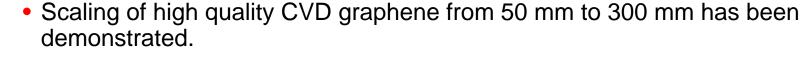
scaling to higher production quantities.

Material applications









- We continue to work on further capacity increases and quality.
- We collaborate to accelerate the commercialization of CVD graphene for a wide range of applications.